

<b>LIST OF REFERENCES CITED BY APPLICANT</b> Form PTO-1449 <i>(use several sheets if necessary)</i>				ATTY. DOCKET NO.:	APPLICATION NO.:		
				4717-7600	10/614,327		
				APPLICANT:			
				Bruno GHYSELEN <i>et al.</i>			
<i>JUL 22 2004</i> Sheet 1 of 1				FILING DATE:	GROUP:		
				July 8, 2003	2822		
<b>U.S. PATENT DOCUMENTS</b>							
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES      NO
<i>MW</i>	B1	10-209453	08/1988	JP (w/English abstract)			X
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
<i>MW</i>	C1	E.A. Fitzgerald et al., <i>Relaxed Ge<sub>x</sub>Si<sub>1-x</sub> structures for III-V integration with Si and high mobility two-dimensional electron gases in Si</i> ; <i>J.Vac.Sci.Technol</i> ; B 10(4), Jul/Aug 1992; pp. 1807-1819.					
<i>MW</i>	C2	R. Egloff et al., <i>Evaluation of Strain Sources in Bond and Etchback Silicon-on-Insulator</i> ; <i>Philips Journal of Research</i> ; Vol. 49, No. 1/2 1995; pp125-138.					
<i>MW</i>	C3	Cher Ming Tan et al., <i>Temperature and Stress Distribution in the SOI Structure During Fabrication</i> ; <i>ZIEEE Transactions on Semiconductor Manufacturing</i> , Vol. 16, No. 2, May 2003; pp. 314-317.					
EXAMINER <i>MW/leczuski</i>				DATE CONSIDERED <i>9/2004</i>			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Sheet 1 of 1				FILING DATE:	GROUP:		
				Concurrently herewith			
<b>U.S. PATENT DOCUMENTS</b>							
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MW	A	6,573,126	06/2003	Cheng et al.	438	149	
MW	B	6,524,935	02/2003	Canaperi et al.	438	478	
MW	C	6,410,371	06/2002	Yu et al.	438	151	
MW	D	6,403,450	06/2002	Maleville et al.	438	471	
MW	E	6,323,108	11/2001	Kub et al.	438	458	
MW	F	6,059,895	05/2000	Chu et al.	148	33.1	
MW	G	5,882,987	03/1999	Srikrishnan	438	458	
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES
							NO
MW	H	02/33746	04/2002	WO			
MW	I	2 365 214	02/2002	Great Britain			
MW	J	01/99169	12/2001	WO			
MW	K	01/11930	02/2001	WO			
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
MW	L	L.J. Huang et al., SiGe-On-Insulator Prepared by Wafer Bonding and Layer Transfer for High Performance Field-Effect Transistors, Applied Physics Letters, February 26, 2002, Vol 78, No. 9					
EXAMINER		<i>MWilczewski</i>		DATE CONSIDERED <i>9/2004</i>			
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